АС ЭНЕРГИЯ

Тиристорный модуль
АМКТ 26

V_{RSM} V	V_{RRM}, V_{DRM} V	I_{TRMS} = 50 A (maximum value for continuous operation) I_{TAV} = 32 A (sin 180; T_C = 68 °C)	
500	400	–	AMKH 26-04D
700	600	AMKT 26-06D	AMKH 26-06D
900	800	AMKT 26-08D	AMKH 26-08D
1300	1200	AMKT 26-12E	AMKH 26-12E
1500	1400	AMKT 26-14E	AMKH 26-14E
1700	1600	AMKT 26-16E	AMKH 26-16E

Symbol	Conditions	AMKT 26 AMKH 26	Units
I_{TAV}	sin. 180; T_{case} = 68 °C	32	A
	T_{case} = 85 °C	25	A
I_D	B2/B6 T_{amb} = 45 °C; P 3/180	38	A
	T_{amb} = 35 °C; P 3/180 F	60	A
I_{RMS}	W1/W3 T_{amb} = 45 °C; P 3/180	52 / 3 x 37	A
I_{TSM}	T_{vj} = 25 °C; 10 ms	550	A
	T_{vj} = 125 °C; 10 ms	480	A
i^2t	T_{vj} = 25 °C; 8,3 ... 10 ms	1 500	A^2s
	T_{vj} = 125 °C; 8,3 ... 10 ms	1 150	A^2s
t_{gd}	T_{vj} = 25 °C; I_G = 1 A		
	di_G/dt = 1 A/µs	1	µs
t_{gr}	$V_D = 0{,}67 \cdot V_{DRM}$	1	µs
$(di/dt)_{cr}$	T_{vj} = 125 °C	150	A/µs
t_q	T_{vj} = 125 °C	typ. 80	µs
I_H	T_{vj} = 25 °C; typ./max.	100	mA
I_L	T_{vj} = 25 °C; R_G = 33 ° ; typ./max.	250	mA
V_T	T_{vj} = 25 °C; I_T = 75 A	max. 1,8	V
$V_{T(TO)}$	T_{vj} = 125 °C	0,9	V
r_T	T_{vj} = 125 °C	12	m°
I_{DD}; I_{RD}	T_{vj} = 125 °C; $V_{RD} = V_{RRM}$		
	$V_{DD} = V_{DRM}$	max. 10	mA
V_{GT}	T_{vj} = 25 °C; d.c.	3	V
I_{GT}	T_{vj} = 25 °C; d.c.	150	mA
V_{GD}	T_{vj} = 125 °C; d.c.	0,25	V
I_{GD}	T_{vj} = 125 °C; d.c.	5	mA
R_{thjc}	cont.	0,9	°C/W
	sin. 180 per thyristor /	0,95	°C/W
	rec. 120 per module	1,0	°C/W
R_{thch}		0,2	°C/W
T_{vj}		–40 ... + 125	°C
T_{stg}		–40 ... + 125	°C
V_{isol}	a.c. 50 Hz; r.m.s; 1 s/1 min	3600	V~
M_1	to heatsink } SI (US) units	5 (44 lb. in.) ± 15 %[2)]	Nm
M_2	to terminals } SI (US) units	3 (26 lb. in.) ± 15 %	Nm
a		$5 \cdot 9{,}81$	m/s^2
w	approx.	95	g

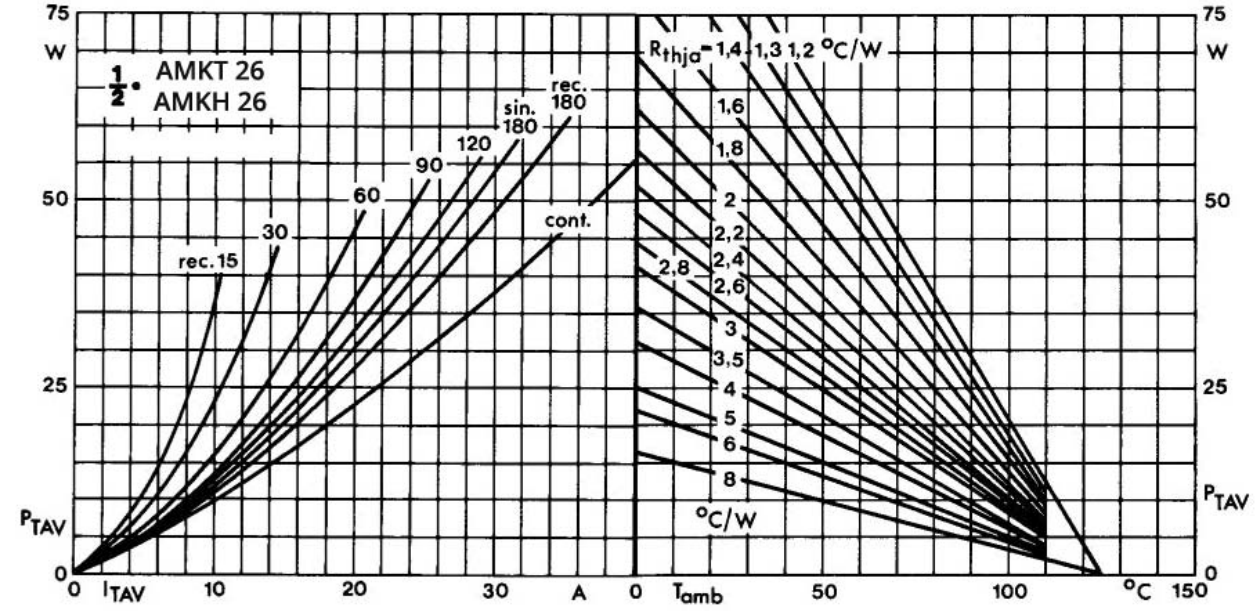

Fig. 1 Power dissipation per thyristor vs. on-state current and ambient temperature

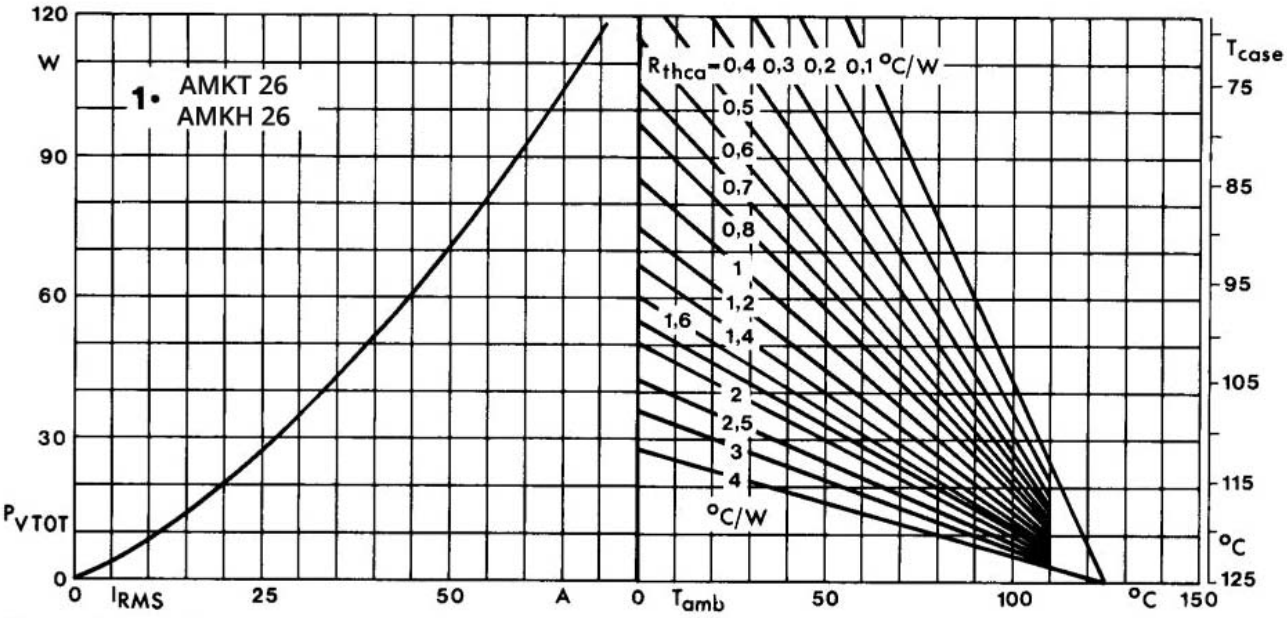

Fig. 2 Power dissipation per module vs. rms current and case temperature

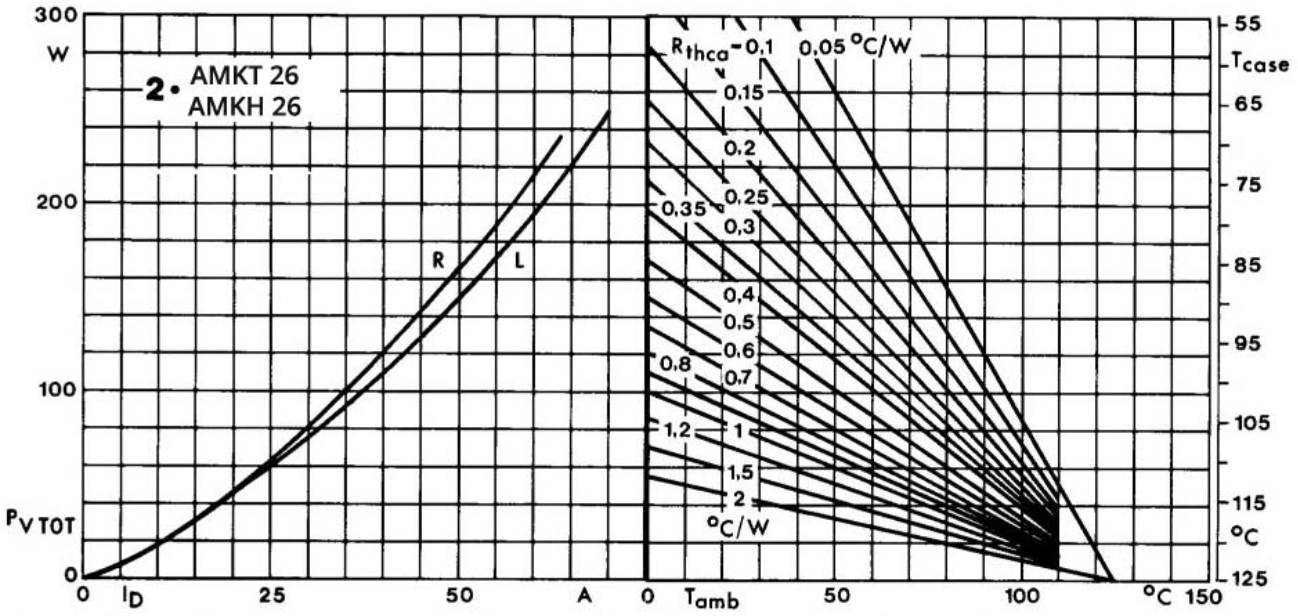

Fig. 3 Power dissipation of two modules vs. direct current and case temperature

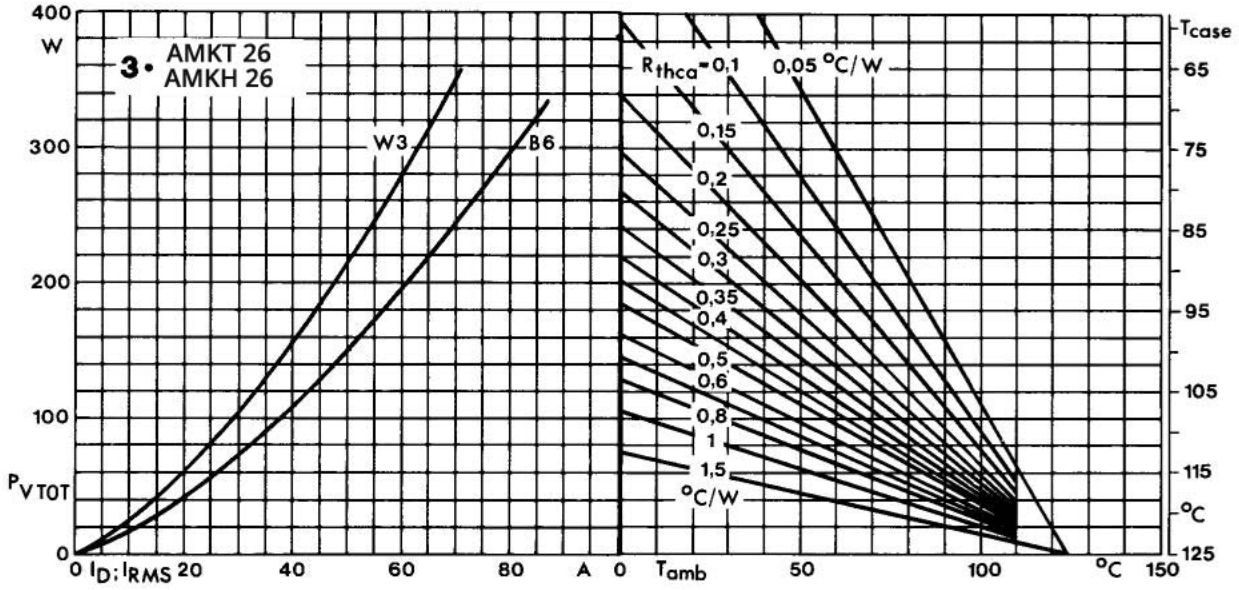

Fig. 4 Power dissipation of three modules vs. direct and rms current and case temperature

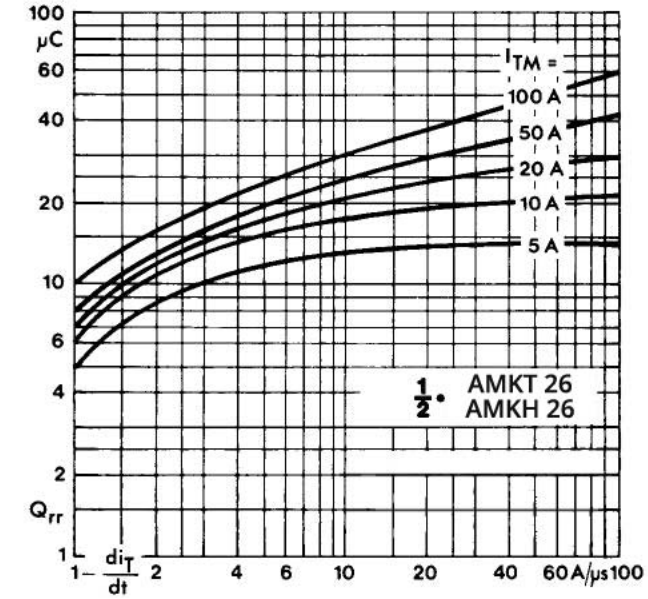

Fig. 5 Recovered charge vs. current decrease

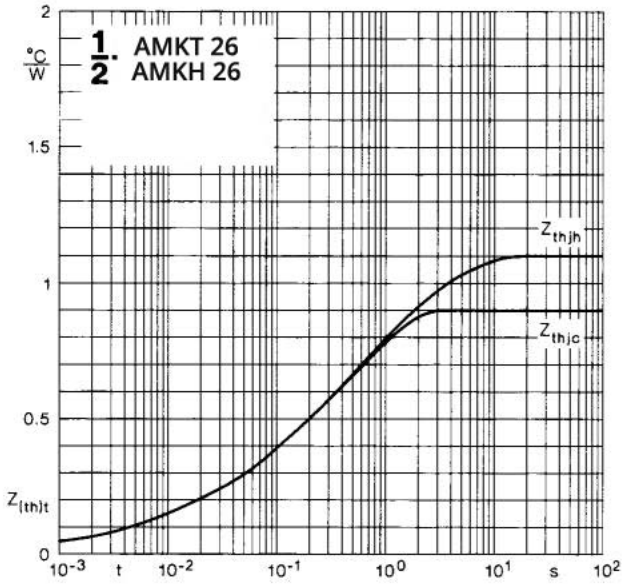

Fig. 6 Transient thermal impedance vs. time

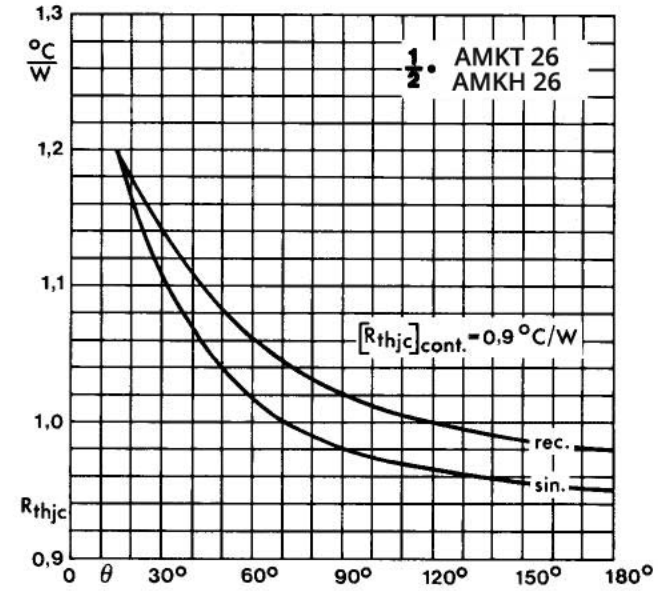

Fig. 7 Thermal resistance vs. conduction angle

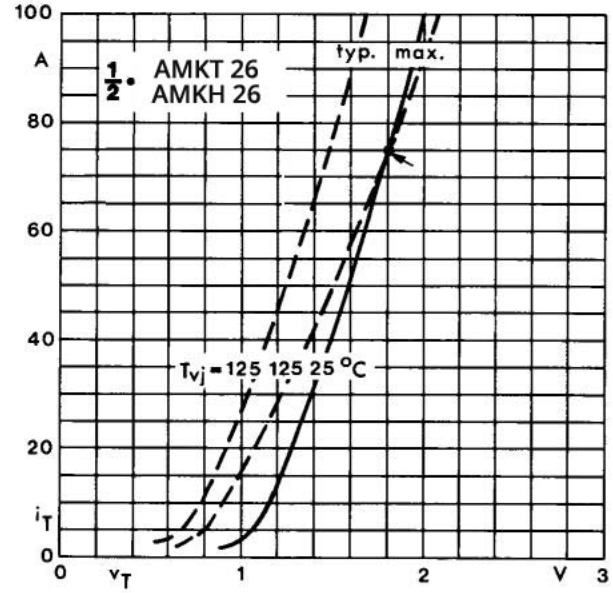

Fig. 8 On-state characteristics

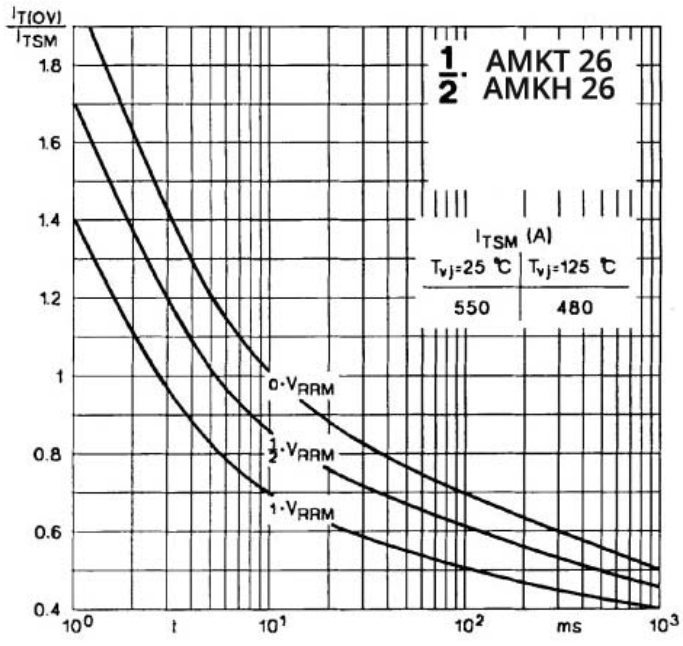

Fig. 9 Surge overload current vs. time

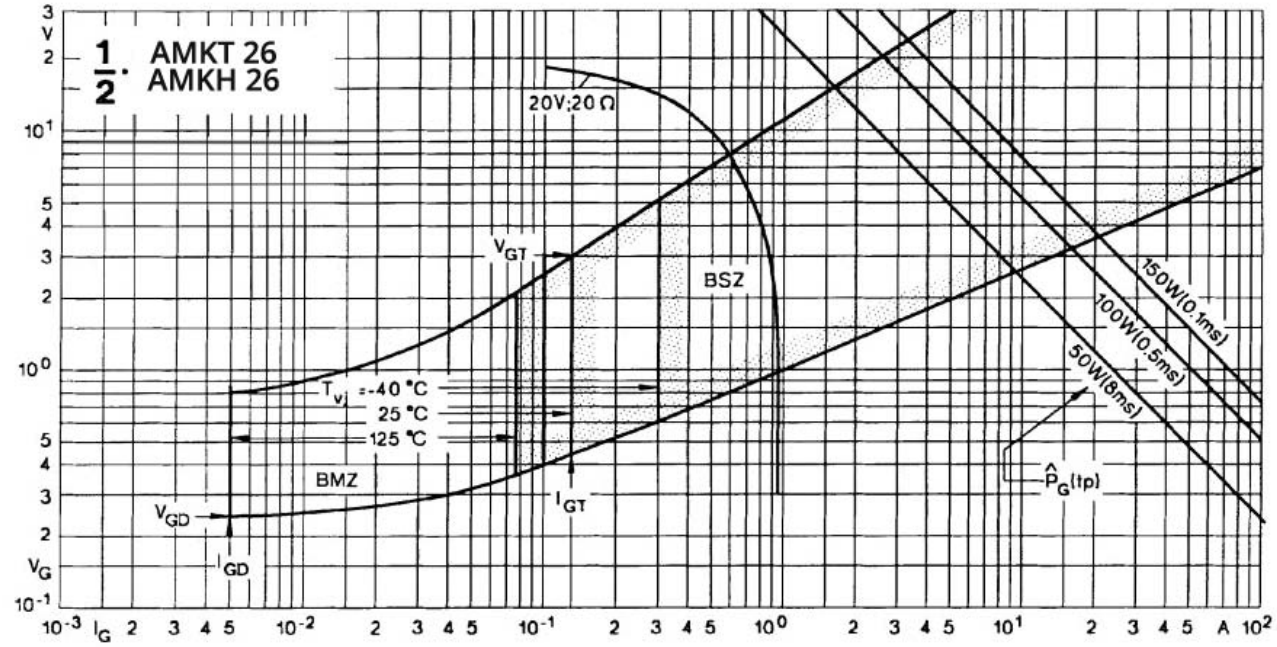

Fig. 10 Gate trigger characteristics

DIMENSIONS

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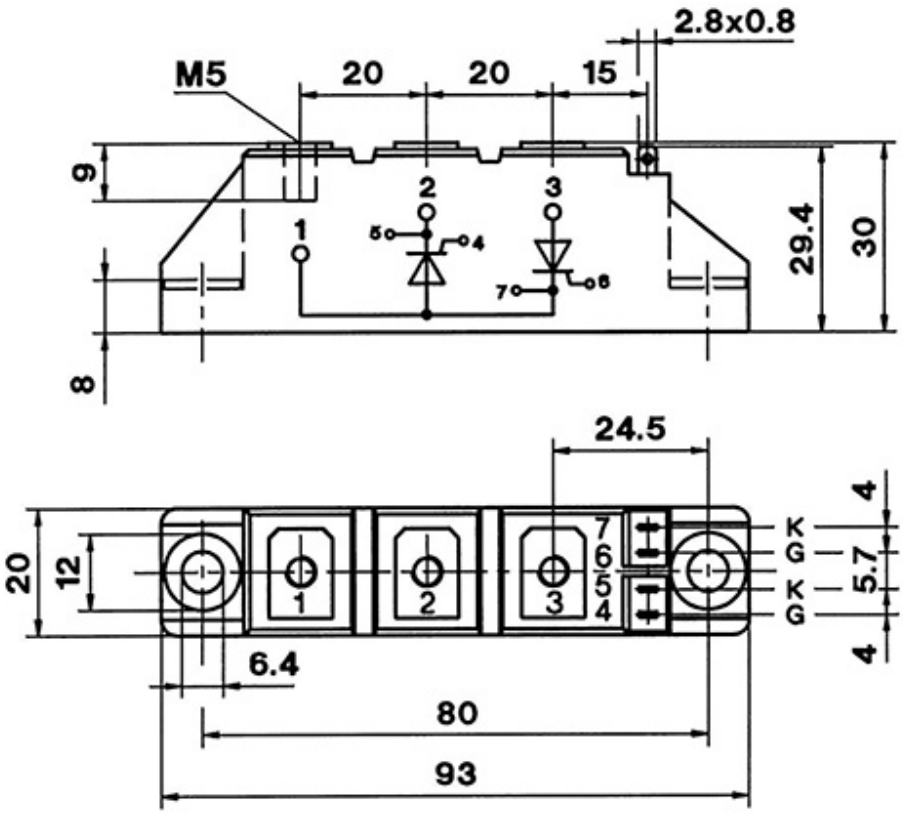

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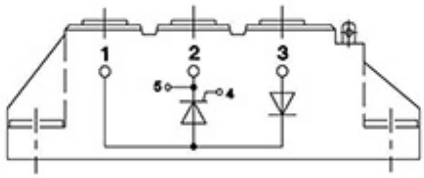
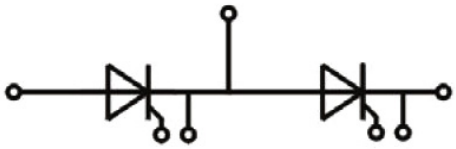


Dimensions in mm

TOPOLOGY OF INTERNAL CONNECTION



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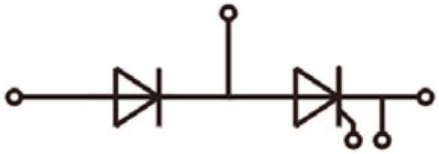

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